

transistor is electrically connected to said second signal line through at least said first thin film transistor;

a voltage supply line formed over said substrate;

a pixel electrode formed over said substrate wherein said pixel electrode is connected to said voltage supply line through at least said second thin film transistor; and

D a driving circuit formed over said substrate for driving at least one of said first and second thin film transistors, said driving circuit comprising a third thin film transistor wherein a channel forming region of said third thin film transistor comprises crystalline silicon,

said method comprising a step of applying a voltage from said voltage supply line to said pixel electrode for a period during one frame, wherein said period is determined in accordance with a desired tone of a display.

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8. (Twice Amended) An operation method of a semiconductor device comprising:

a substrate having an insulating surface;

a first signal line extending over said substrate;

a first bottom gate type thin film transistor having a channel region comprising crystalline silicon formed over said substrate wherein a gate of said first thin film transistor is connected to said first signal line;

DD a second signal line extending across said first signal line;

a second bottom gate type thin film transistor having a channel region comprising crystalline silicon formed over said substrate wherein a gate of said second thin film transistor is electrically connected to said second signal line through at least said first thin film transistor;

a voltage supply line formed over said substrate;

a pixel electrode formed over said substrate wherein said pixel electrode is connected to said voltage supply line through at least said second thin film transistor; and

a driving circuit formed over said substrate for driving at least one of said first and second thin film transistors, said driving circuit comprising a third thin film transistor wherein a channel forming region of said third thin film transistor comprises crystalline silicon,

wherein a channel width of said second thin film transistor is larger than a channel width of said first thin film transistor,

said method comprising a step of applying a voltage from said voltage supply line to said pixel electrode for a period during one frame, wherein said period is determined in accordance with a desired tone of a display.

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52. (Amended) The method according to claim 36 wherein said semiconductor device is a liquid crystal device.

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55. (Amended) The method according to claim 3 wherein said semiconductor device is a liquid crystal device.

56. (Amended) The method according to claim 6 wherein said semiconductor device is a liquid crystal device.

57. (Amended) The method according to claim 9 wherein said semiconductor device is a liquid crystal device.

58. (Amended) The method according to claim 15 wherein said semiconductor device is a liquid crystal device.

59. (Amended) The method according to claim 18 wherein said semiconductor device is a liquid crystal device.

60. (Amended) The method according to claim 27 wherein said semiconductor device is a liquid crystal device.

61. (Amended) The method according to claim 30 wherein said semiconductor device is a liquid crystal device.

62. (Amended) The method according to claim 33 wherein said semiconductor device is a liquid crystal device.

63. (Amended) The method according to claim 36 wherein said semiconductor device is a liquid crystal device.

64. (Amended) The method according to claim 39 wherein said semiconductor device is a liquid crystal device.

65. (Amended) The method according to claim 42 wherein said semiconductor device is a liquid crystal device.

66. (Amended) The method according to claim 45 wherein said semiconductor device is a liquid crystal device.

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